

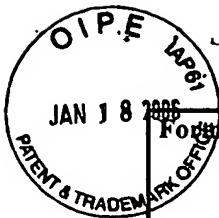


Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No.	Application No.:
	NOVLP090/NVLS-2888	10/733,858
	Applicant:	
	Zhu et al.	
	Filing Date	Group
	December 10, 2003	2891

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
78/CS	A1	6,200,412	03.2001	Kilgore et al.			
	A2	6,232,196	5/12/01	Raaijmakers et al.			
	A3	2003/0207580	11/6/03	Li et al.			
	A4	5,384,068	11/10/98	Chern et al.			
	A5	2004/0082181	4/29/04	Doan et al.			
	A6	6,596,653	7/22/03	Tan et al.			
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	A26	5,516,729	05.1996	Dawson et al.			
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	A28	6,077,574	06.2000	Usami			
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	A33	2003/0165632	09.2003	Lin et al.			
Examiner	78/CS			Date Considered	11/2/06		

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub- class	Translation	
							Yes	No
ZSKS	B1	JP 2003-031,649	01.2003	Japan				

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
ZSKS	C1	U.S. Office Action mailed August 6, 2003, from U.S. Application No. 10/058,897. [Atty Dckt. NOVLP040X1/NVLS-000607]
	C2	U.S. Office Action mailed January 29, 2004, from U.S. Application No. 10/058,897. [Atty Dckt. NOVLP040X1/NVLS-000607]
	C3	U.S. Office Action mailed May 21, 2004, from U.S. Application No. 10/058,897. [Atty Dckt. NOVLP040X1/NVLS-000607]
	C4	U.S. Office Action mailed August 10, 2004, from U.S. Application No. 10/271,333. [Atty Dckt. NOVLP054/NVLS-000719]
	C5	U.S. Office Action mailed April 14, 2004, from U.S. Application No. 10/271,333. [Atty Dckt. NOVLP054/NVLS-000719]
	C6	U.S. Office Action mailed June 29, 2005, from U.S. Application No. 10/728,569. [Atty Dckt. NOVLP087/NVLS-2880]
	C7	Papasoulitis et al., "Hydrogen-Based Phosphosilicate Glass Process for Gap Fill of High Aspect Ratio Structures", Novellus Systems, Inc., filed October 11, 2002, Application No. 10/271,333, pages 1-28. [Atty Dkt No. NOVLP054/NVLS-000719].
	C8	Guari et al., "Method of Preventing Structures Erosion During Multi-Step Gap Fill", Novellus Systems, Inc., filed December 4, 2003, Application No. 10/728,569, pages 1-29. [Atty Dkt No. NOVLP087/NVLS-2880].
	C9	U.S. Office Action mailed January 7, 2005, from U.S. Application No. 10/728,569. [Atty Dckt. NOVLP087/NVLS-2880]
	C10	U.S. Office Action mailed November 6, 2002, from U.S. Application No. 09/996,619. [Atty Dckt. NOVLP040/NVLS-000592]
	C11	U.S. Office Action mailed March 2, 2004, from U.S. Application No. 10/442,846. [Atty Dckt. NOVLP040D1/NVLS-000592D1]
	C12	Bayman et al., "Gap Fill For High Aspect Ratio Structures", Novellus Systems, Inc., filed July 13, 2004, Application No. 10/890,655, pages 1-24. [Atty Dkt No. NOVLP040D2/NVLS-000592D2].
	C13	U.S. Office Action mailed July 25, 2005, from U.S. Application No. 10/890,655. [Atty Dckt. NOVLP040D2/NVLS-000592D2]
	C14	U.S. Office Action mailed November 17, 2005, from U.S. Application No. 10/316,987. [Atty Dckt. NOVLP053/NVLS-000706]
Examiner	Date Considered	
ZSKS	11/2/06	

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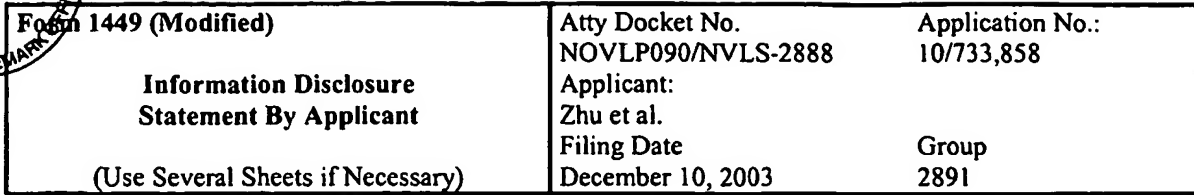


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Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
JSKS	C15	U.S. Office Action mailed April 30, 2004, from U.S. Application No. 10/389,164. [Atty Dkt. NOVLP061/NVLS-000756]
	C16	Sutanto et al., "Method For Controlling Etch Process Repeatability", Novellus Systems, Inc., filed September 2, 2003, Application No. 10/654,113, pages 1-31. [Atty Dkt No. NOVLP079/NVLS-002850].
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	C18	U.S. Office Action mailed December 2, 2004, from U.S. Application No. 10/654,113. [Atty Dkt. NOVLP079/NVLS-002850]
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	C20	Bayman et al., "Process Modulation to Prevent Structure Erosion During Gap Fill", Novellus Systems, Inc., filed September 7, 2004, Application No. 10/935,909, pages 1-30. [Atty Dkt No. NOVLP105/NVLS-2929].
	C21	Papasouliotis et al., "Dynamic Modification of Gap-Fill Process Characteristics", Novellus Systems, Inc., filed September 21, 2004, Application No. 10/947,424, pages 1-25. [Atty Dkt No. NOVLP113/NVLS-2949].
	C22	Hook et al., "The Effects of Fluorine on Parametrics and Reliability in a 0.18- μ m 3.5/6.8 nm Dual Gate Oxide CMOS Technology", IEEE Transactions on Electron Devices, Vol. 48, No. 7, July 2001, pp. 1346-1353.
	C23	Shanker et al., "Hydrogen Treatment Enhanced Gap Fill", Novellus Systems, Inc., filed March 16, 2005, Application No. 11/082,369, pages 1-33. [Atty Dkt No. NOVLP129/NVLS-3055].
	C24	Papasouliotis et al., "Deposition Profile Modification Through Process Chemistry", Novellus Systems, Inc., filed December 9, 2002, Application No. 10/316,987, pages 1-35. [Atty Dkt No. NOVLP053/NVLS-000706].
	C25	U.S. Office Action mailed January 27, 2005, from U.S. Application No. 10/316,987. [Atty Dkt. NOVLP053/NVLS-000706]
	C26	U.S. Office Action mailed July 14, 2005, from U.S. Application No. 10/316,987. [Atty Dkt. NOVLP053/NVLS-000706]
	C27	Lang et al., "Helium-Based Etch Process in Deposition-Etch-Deposition Gap Fill", Novellus Systems, Inc., filed June 22, 2005, Application No. 11/159,834, pages 1-29. [Atty Dkt No. NOVLP135/NVLS-3016].
	C28	Lang et al., "Strain Engineering - HDP Thin Film With Tensile Stress For FEOL and Other Applications", Novellus Systems, Inc., filed November 17, 2004, Application No. 10/991,890, pages 1-35. [Atty Dkt No. NOVLP119/NVLS-2988]
Examiner	Date Considered	
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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